

Plastic-Encapsulate Diodes

SCHOTTKY BARRIER DIODE

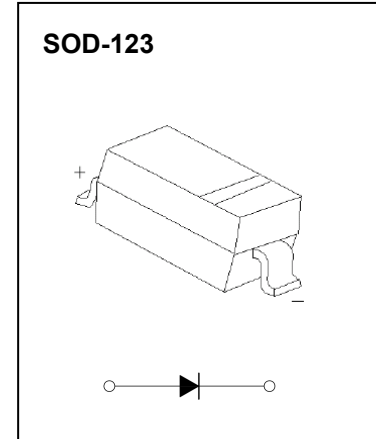
FEATURES

For use in low voltage, high frequency inverters
Free wheeling, and polarity protection applications.

MARKING: B5817W: SJ

B5818W:SK

B5819W: SL



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	B5817W	B5818W	B5819W	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	20	30	40	V
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Rectified Output Current	I_O	1			A
Peak Forward Surge Current @t=8.3ms	I_{FSM}	9			A
Repetitive Peak Forward Current	I_{FRM}	1.5			A
Power Dissipation	P_d	500			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	250			°C/W
Storage Temperature	T_{STG}	-55~+150			°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1mA$ B5817W B5818W B5819W	20 30 40		V
Reverse voltage leakage current	I_R	$V_R=20V$ $V_R=30V$ $V_R=40V$ B5817W B5818W B5819W		1	mA
Forward voltage	V_F	B5817W $I_F=1A$		0.45	V
		$I_F=3A$		0.75	
		B5818W $I_F=1A$		0.55	V
$I_F=3A$		0.875			
B5819W $I_F=1A$		0.6	V		
$I_F=3A$		0.9			
Diode capacitance	C_D	$V_R=4V, f=1MHz$		120	pF

